



Preliminary

RF2322

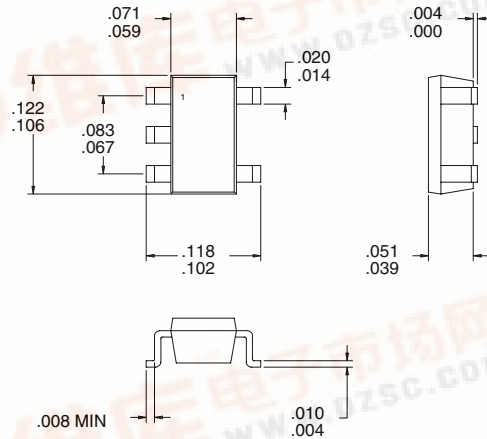
3V GENERAL PURPOSE AMPLIFIER

**Typical Applications**

- Broadband Gain Blocks
- Final PA for Low-Power Applications
- IF or RF Buffer Amplifiers
- Driver Stage for Power Amplifiers
- Oscillator Loop Amplifiers

**Product Description**

The RF2322 is a general purpose, low-cost silicon amplifier designed for operation from a 3V supply. The circuit configuration with resistive feedback allows for broadband cascadable amplification. Capacitive compensation extends the bandwidth of the amplifier and input stage design optimizes noise figure. The device is unconditionally stable and internally matched to 50Ω. The only external components required for specified performance are bypass and DC blocking capacitors (as shown in application schematic). The RF2322 is available in a very small industry-standard SOT-23 5-lead surface mount package, enabling compact designs which conserve board space.



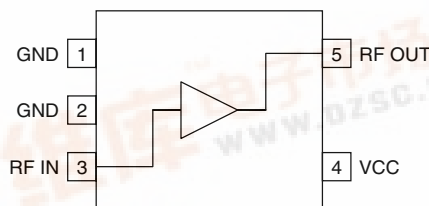
**Optimum Technology Matching® Applied**

- Si BJT
- GaAs HBT
- GaAs MESFET
- Si Bi-CMOS
- SiGe HBT
- Si CMOS

**Package Style: SOT-23-5**

**Features**

- DC to >2000MHz Operation
- 2.7V to 3.3V Single Supply
- +3dBm Output IP3
- 19dB Gain at 900MHz
- 12dB Gain at 1900MHz
- High Isolation (38dB at 900MHz)



**Functional Block Diagram**

**Ordering Information**

- RF2322 3V General Purpose Amplifier
- RF2322 PCBA Fully Assembled Evaluation Board

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GENERAL PURPOSE AMPLIFIERS



## Absolute Maximum Ratings

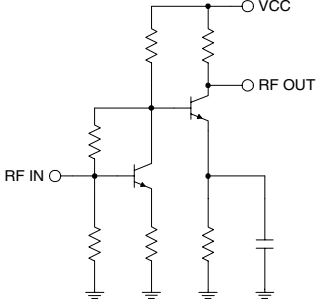
Parameter	Rating	Unit
Supply Voltage	4.0	V
Operating Ambient Temperature	-40 to +85	°C
Storage Temperature	-40 to +150	°C



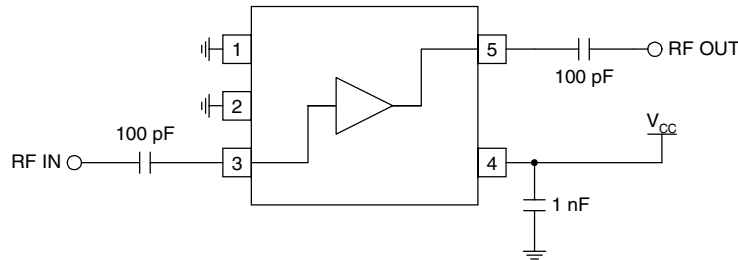
Caution! ESD sensitive device.

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Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Overall</b>					T=27°C, V <sub>CC</sub> =3.0V
Frequency Range		DC to >2000		MHz	
<b>100MHz Performance</b>					T=27°C, V <sub>CC</sub> =3.0V
Gain		20		dB	
Noise Figure		3.2		dB	
Output IP3		4		dBm	
Output P <sub>1dB</sub>		-8		dBm	
Input Return Loss		19		dB	
Output Return Loss		11		dB	
Isolation		55		dB	
<b>500MHz Performance</b>					T=27°C, V <sub>CC</sub> =3.0V
Gain		20		dB	
Noise Figure		3.4		dB	
Output IP3		4		dBm	
Output P <sub>1dB</sub>		-8		dBm	
Input Return Loss		18		dB	
Output Return Loss		9		dB	
Isolation		45		dB	
<b>900MHz Performance</b>					T=27°C, V <sub>CC</sub> =3.0V
Gain		19		dB	
Noise Figure		3.3		dB	
Output IP3		3		dBm	
Output P <sub>1dB</sub>		-7		dBm	
Input Return Loss		13		dB	
Output Return Loss		8		dB	
Isolation		38		dB	
<b>1000MHz Performance</b>					T=27°C, V <sub>CC</sub> =3.0V
Gain		19		dB	
Noise Figure		3.2		dB	
Output IP3		3		dBm	
Output P <sub>1dB</sub>		-8		dBm	
Input Return Loss		12		dB	
Output Return Loss		8		dB	
Isolation		35		dB	
<b>2000MHz Performance</b>					T=27°C, V <sub>CC</sub> =3.0V
Gain		12		dB	
Noise Figure		4.0		dB	
Output IP3		2		dBm	
Output P <sub>1dB</sub>		-8		dBm	
Input Return Loss		11		dB	
Output Return Loss		15		dB	
Isolation		26		dB	
<b>Power Supply</b>					
Operating Voltage		3.0±10%		V	
Operating Current		7.5		mA	V <sub>CC</sub> =3.0V

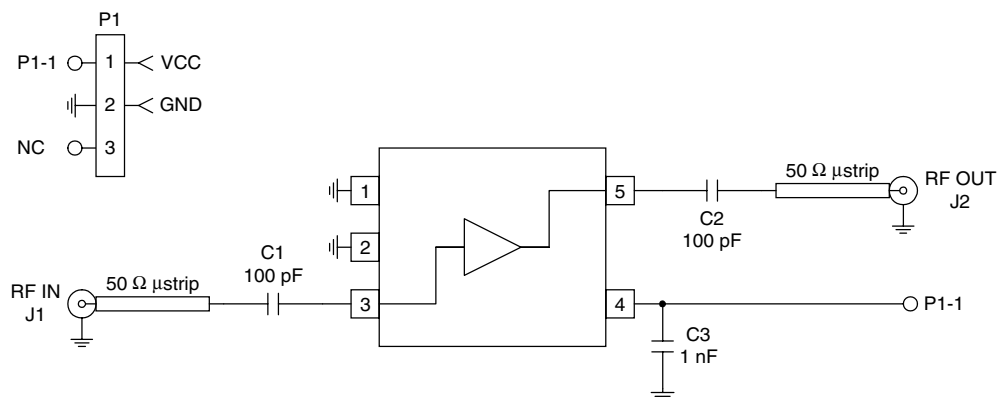
Pin	Function	Description	Interface Schematic
1	GND	Ground connection. Keep traces physically short and connect immediately to ground plane for best performance.	
2	GND	Same as pin 1.	
3	RF IN	RF input pin. This pin is not internally DC blocked and thus requires an external blocking capacitor suitable for the frequency of operation. The input impedance of this pin is internally matched to 50Ω using resistive feedback.	
4	VCC	Supply connection. This pin should be bypassed with a suitable capacitor(s).	
5	RF OUT	RF output and bias pin. The output impedance of this pin is internally matched to 50Ω using resistive feedback. Because DC biasing is present on this pin, a DC blocking capacitor should be used in most applications (see application schematic).	See pin 3 schematic.

### Application Schematic

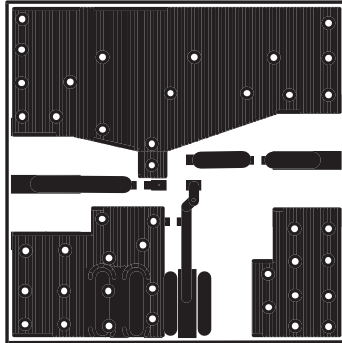
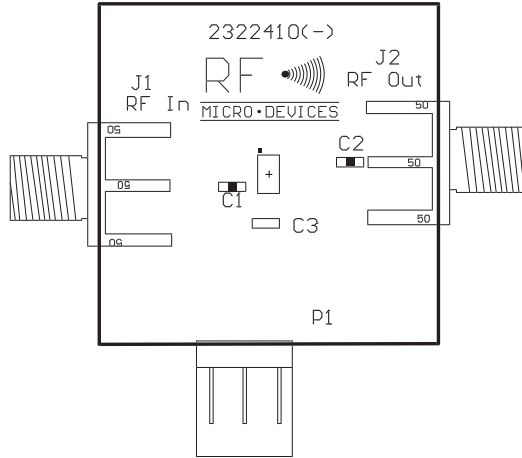


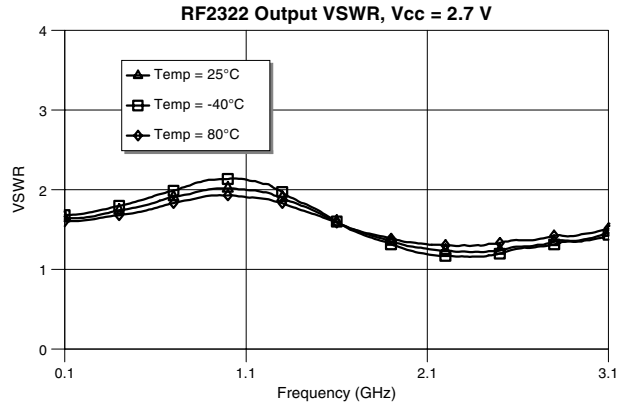
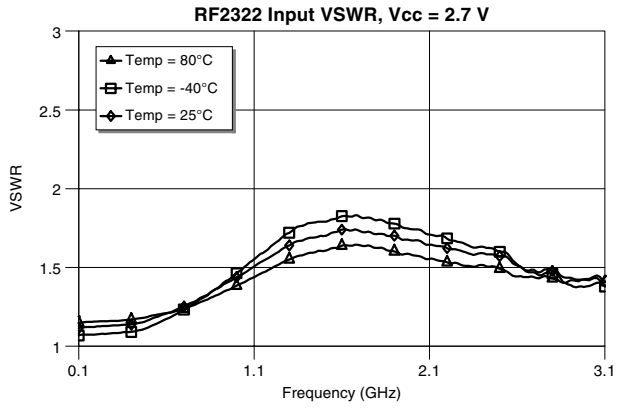
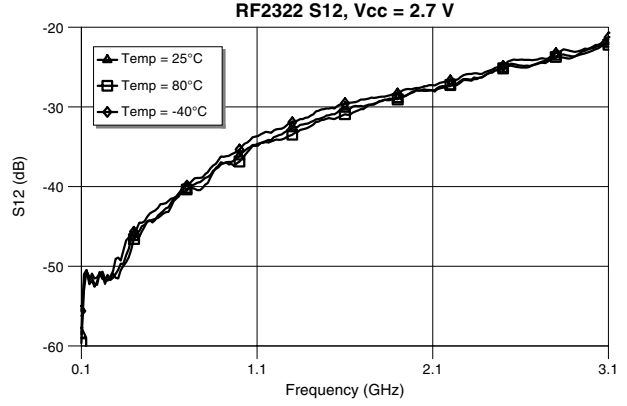
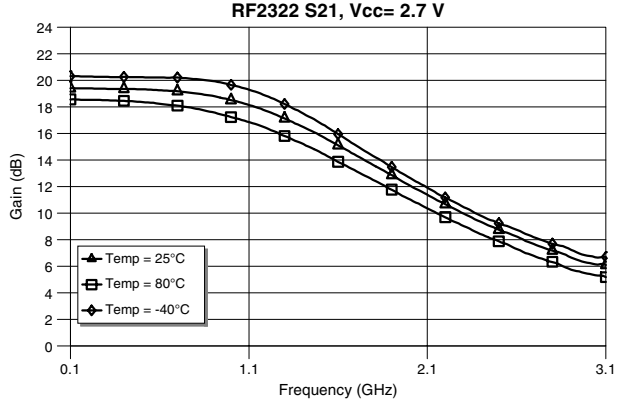
### Evaluation Board Schematic

(Download [Bill of Materials](http://www.rfmd.com) from [www.rfmd.com](http://www.rfmd.com).)

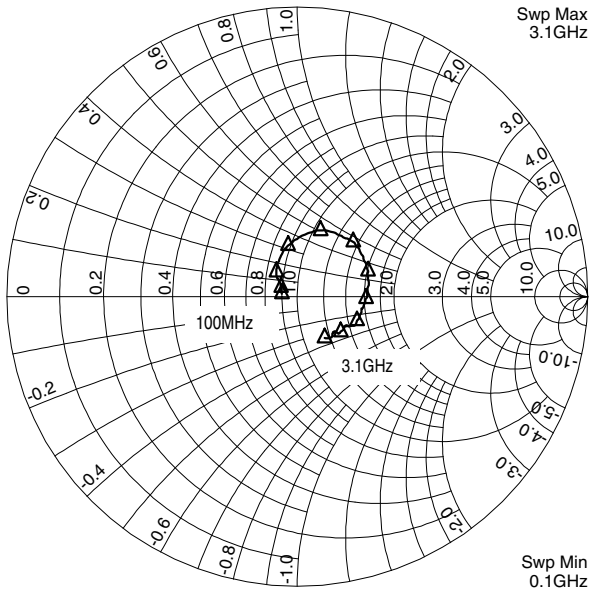


### Evaluation Board Layout 1" x 1"

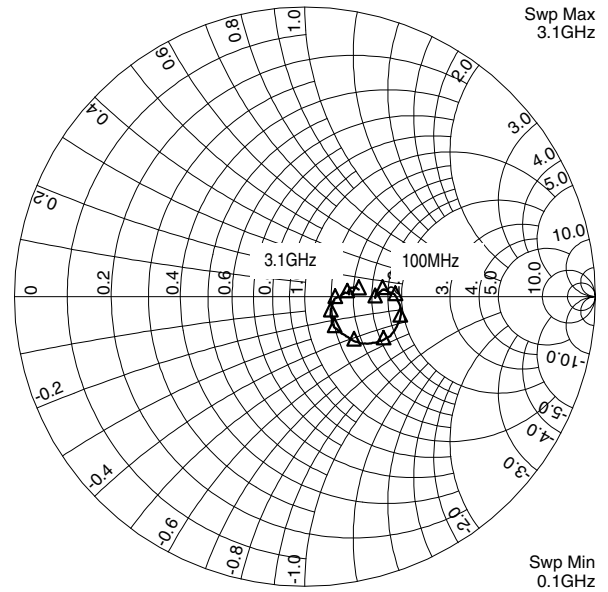


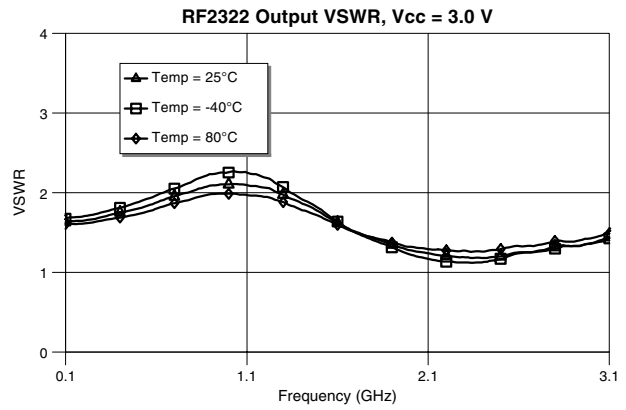
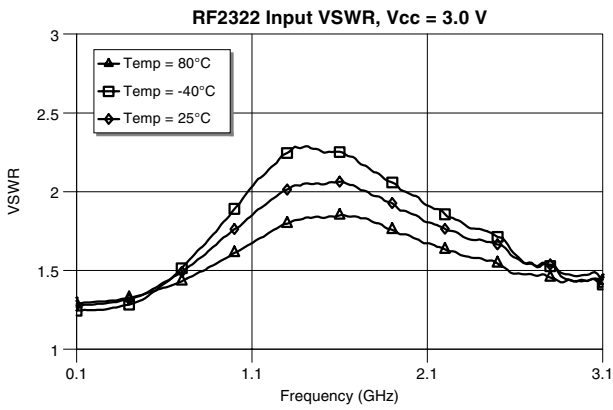
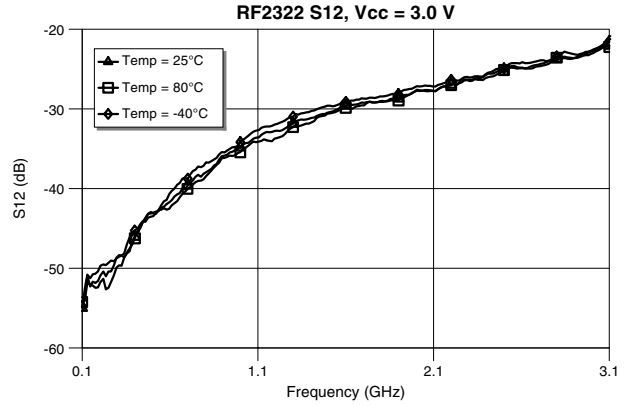
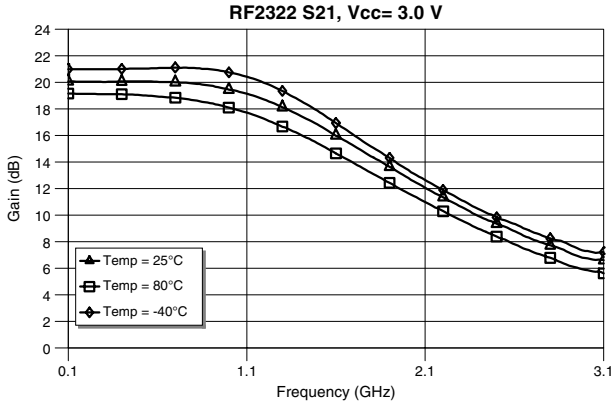


**RF2322 S11, Vcc = 2.7 V, Temp = 25°C**

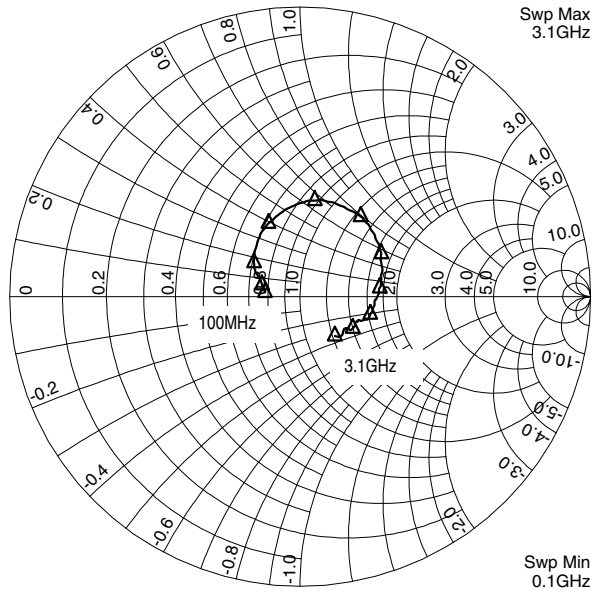


**RF2322 S22, Vcc = 2.7 V, Temp= 25°C**

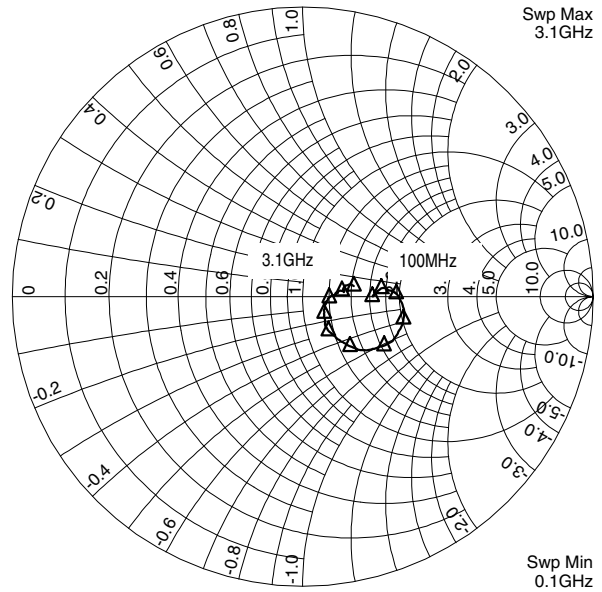


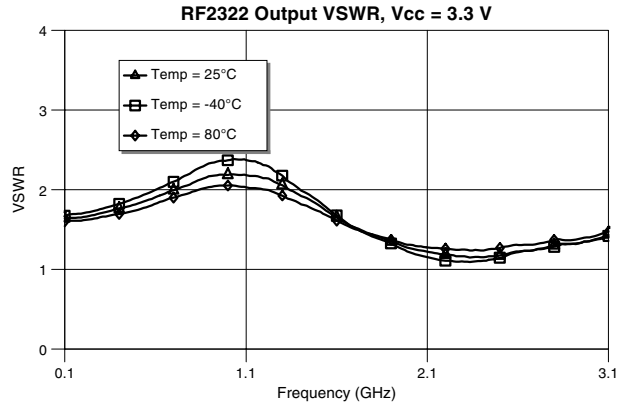
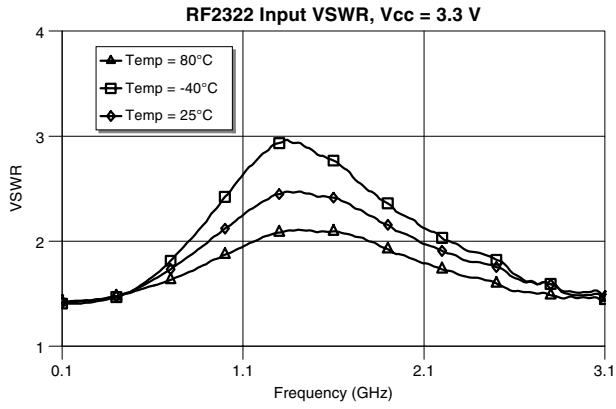
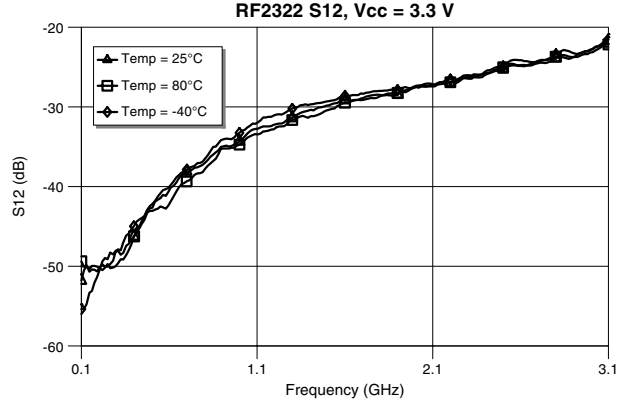
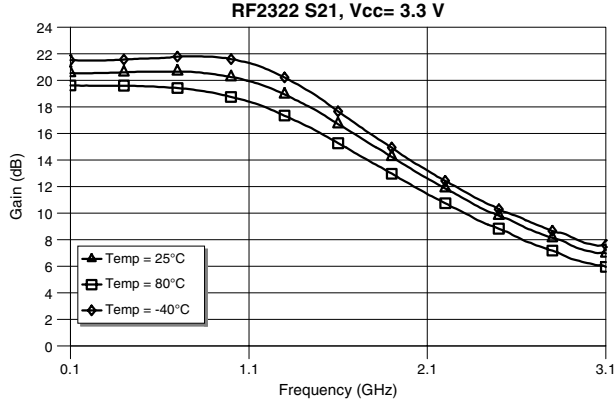


**RF2322 S11, Vcc = 3.0 V, Temp = 25°C**

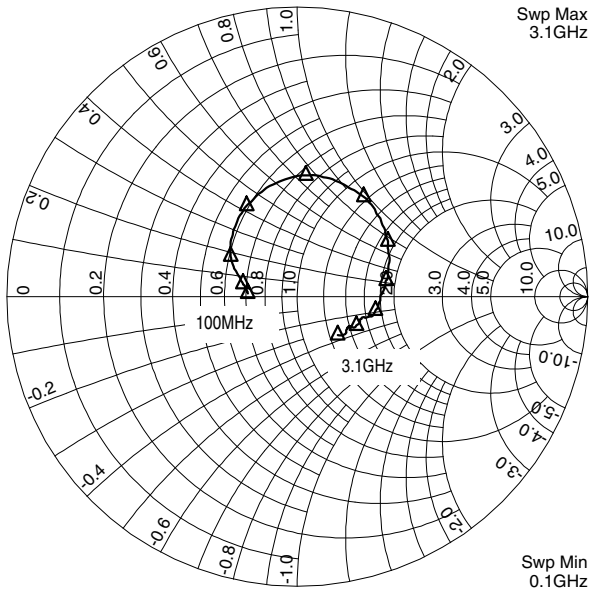


**RF2322 S22, Vcc = 3.0 V, Temp = 25°C**

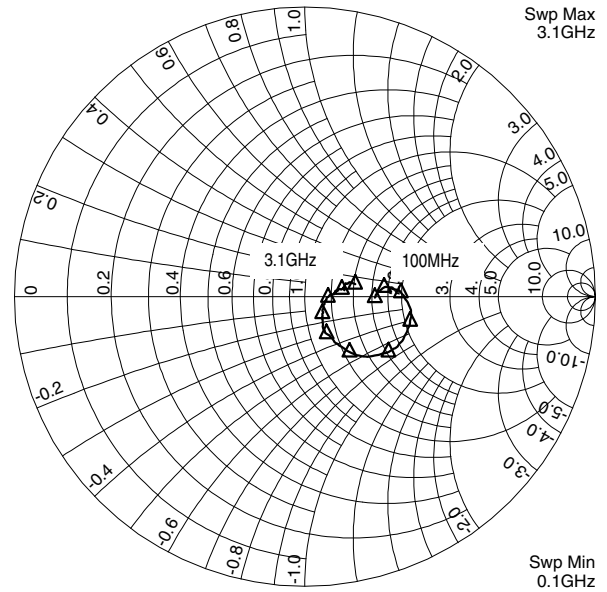




**RF2322 S11, Vcc = 3.3 V, Temp = 25°C**



**RF2322 S22, Vcc = 3.3 V, Temp= 25°C**



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